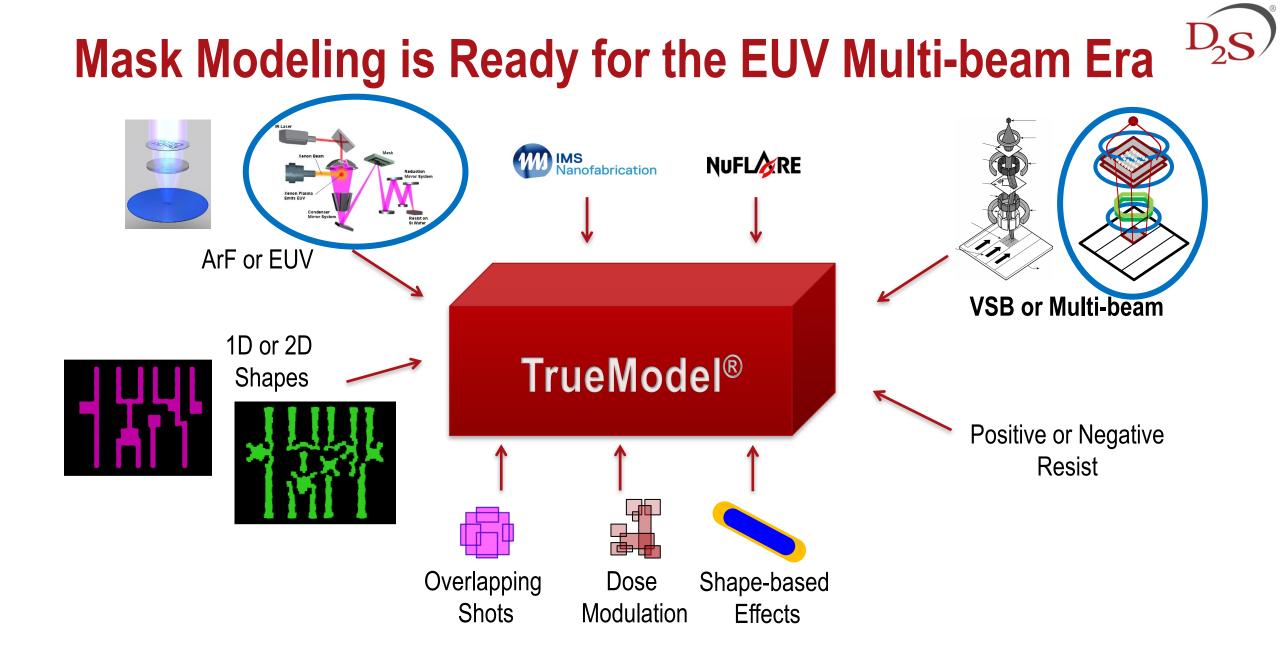


## EUV Modeling in the Multi-beam Mask Writing Era

Ryan Pearman, Harold Zable, Aki Fujimura D<sub>2</sub>S, Inc.

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#### Talk flow... What is challenging about EUV multi-beam modeling:

- Review the challenges about the multi-beam era
- Review the challenges about the EUV era
- Demonstrate that the two challenges can co-exist
  - But only with help from GPUs!

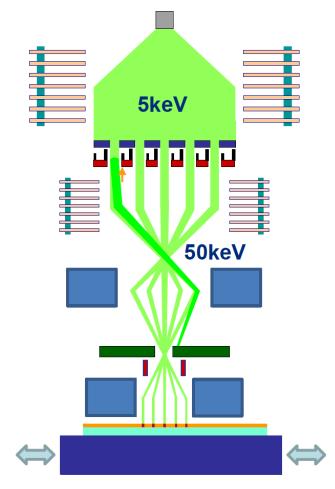


# Reviewing the Complexities in the Multi-beam Era

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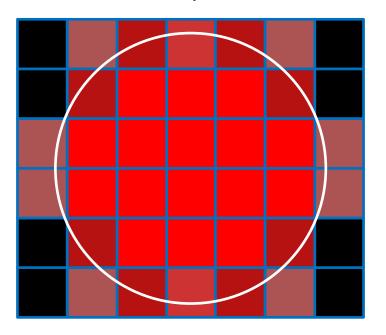
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### **Multi-beam Uses Many Beamlets in Parallel**



Source: IMS Nanofabrication

Many beamlets means patterns are rasterized



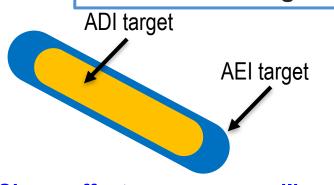
**Dose profiles are more complex than for VSB** 

### **Multi-beam Era is More Complicated**



VSB era	Multi-beam era
Dose profiles are "simple"	Dose profiles will be complex
Typically only "1 or 2" doses assigned	Many dose values to predict ["0" "2"]
Can use dose terms to assist bias terms.	Dose terms no longer degenerate to Etch terms; more complex dose models are needed
Etch done by constant bias	Etch needs to be done on curvilinear shapes

**Curvilinear geometry transformations ideally suited for GPU!** 



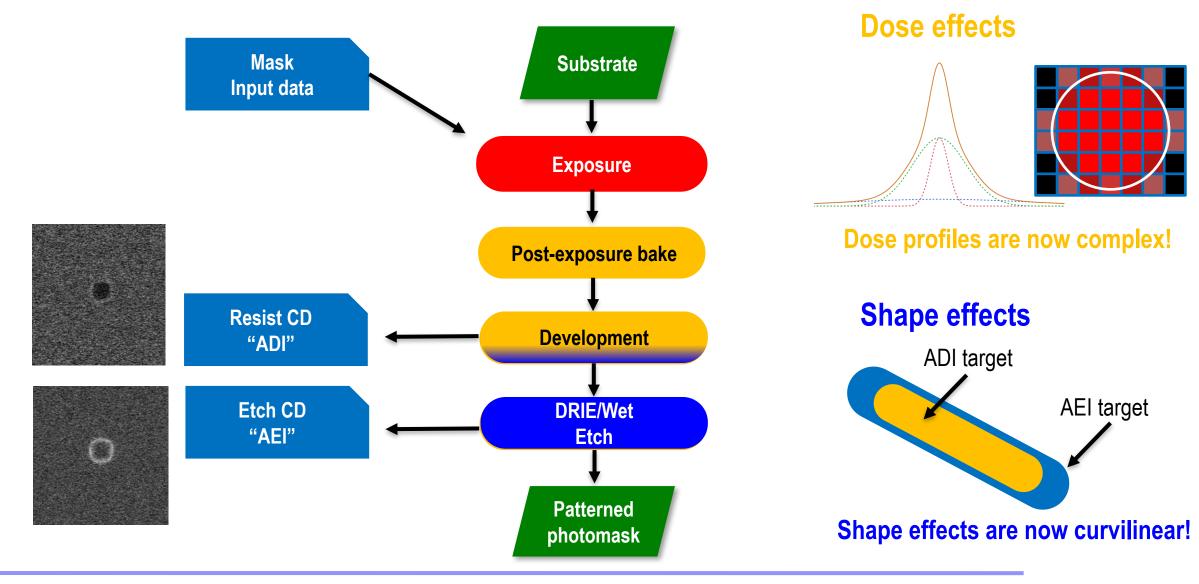
Shape effects depend on:

- Open area "shadowing"
- Local pattern density "loading"
- Local radius of curvature

Shape effects are now curvilinear!

A good etch model needs to encompass a wide variety of 2D features

# Mask Modeling Must Separate Dose and Shape Effects $^{\mathrm{D}_{2}\mathrm{S}/}$



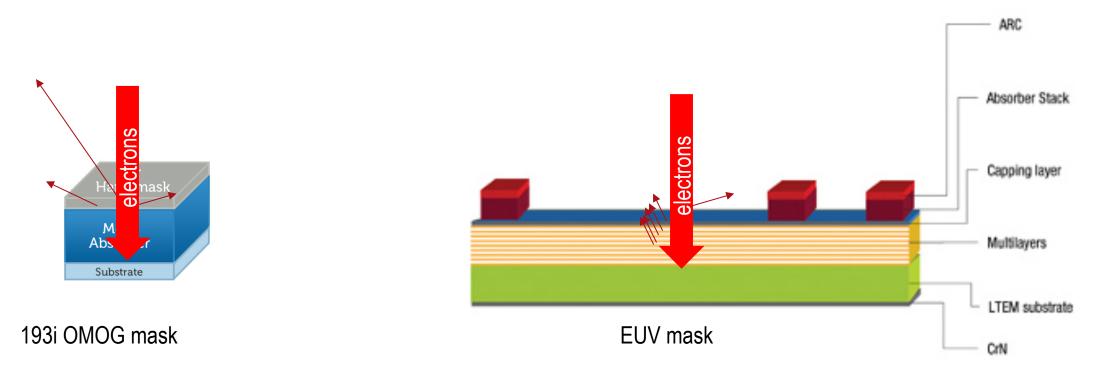


# Reviewing the Complexities in the EUV Era

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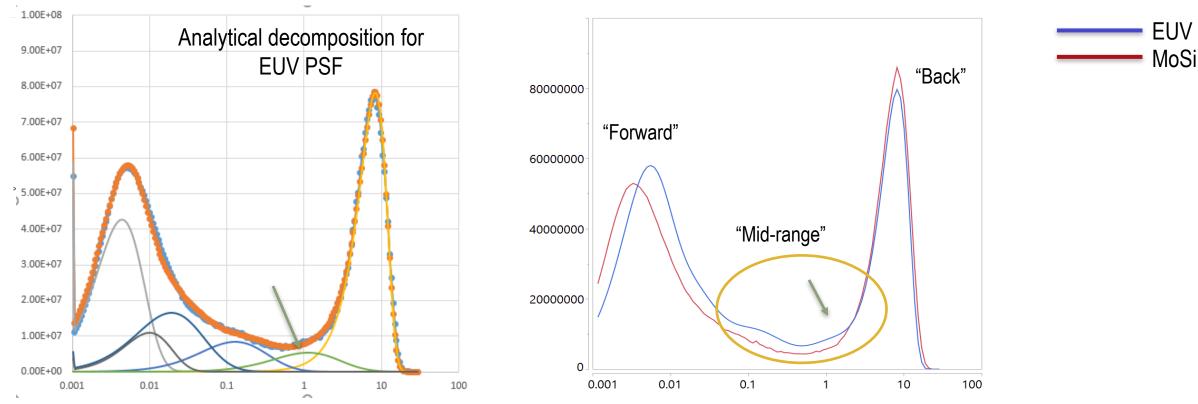
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### eBeam Scattering is More Complex in EUV



#### Electrons scatter off of each interface There are many more interfaces in the EUV mask stack More interfaces = broader scattering

### EUV has the Well-Known "Mid-range" Effect

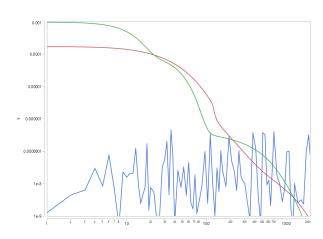


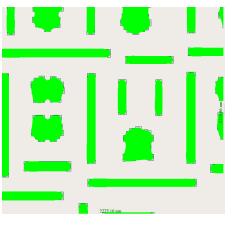
In addition to the standard <n>G model, a ~1um "exponential" kernel needs to be added: In reality, a sum of Gaussians is no longer accurate enough for EUV modeling Correction runtime concern: length scale are larger than just "forward scattering"



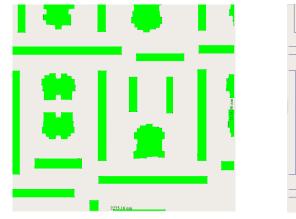
### **GPU Modeling Enables Arbitrary PSF**

- If you compute using GPUs, the PSF can be read into a texture
  Runtime is independent of PSF choice (Gaussian, or more complex)
- Can use the PSF from first principles directly
  - Can use analytical approximations to it (<n>G + 1E)
  - Can even use random numbers





25nm blurred MC-Sim PSF



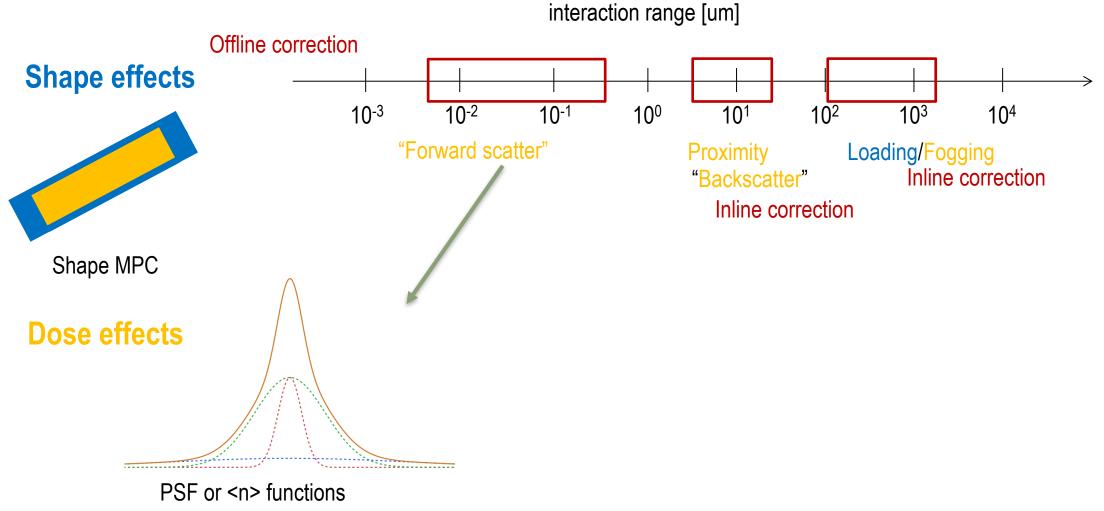
Analytical EUV PSF



### **Mask Process Modeling/Correction**



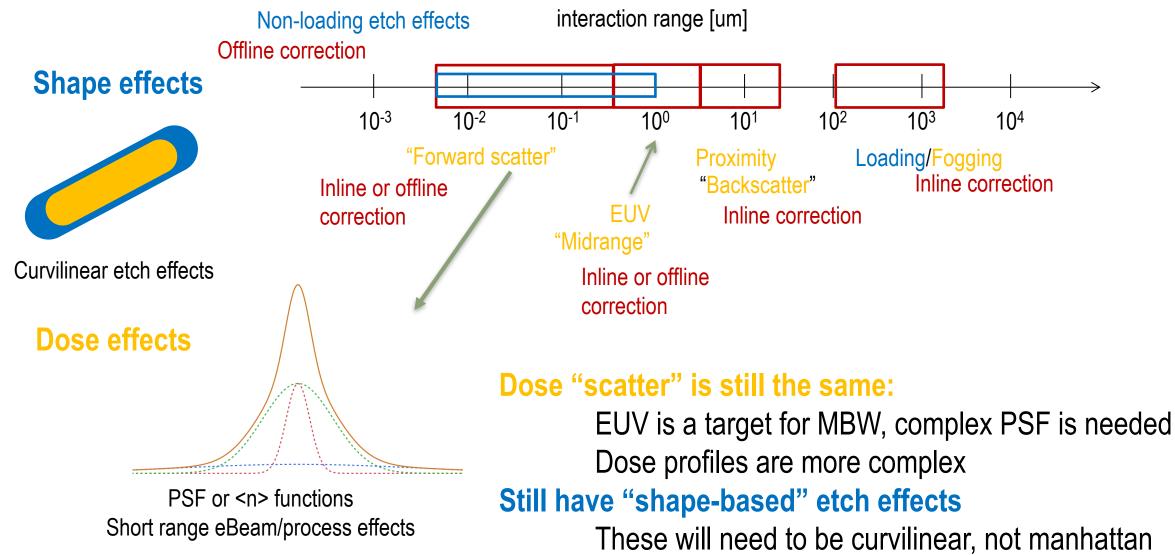
#### **VSB** era corrections



Short range eBeam/process effects

# **Mask Process Modeling/Correction**

#### In the Multi-beam Mask Writing Era





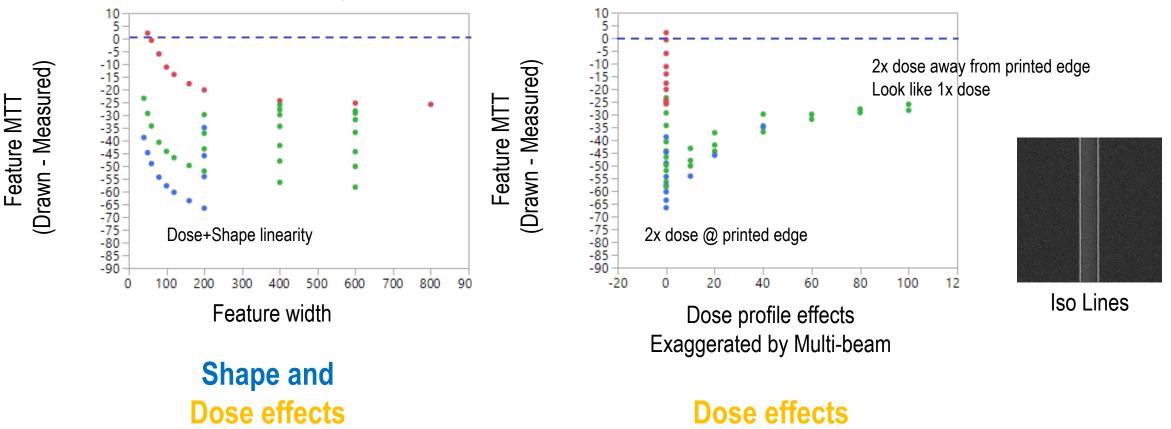
### Integrating EUV and Multi-beam Modeling

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### **193i Mask Data Exhibit Both Shape and Dose Effects**

Non-zero y-axis values mean: mask print errors if uncorrected

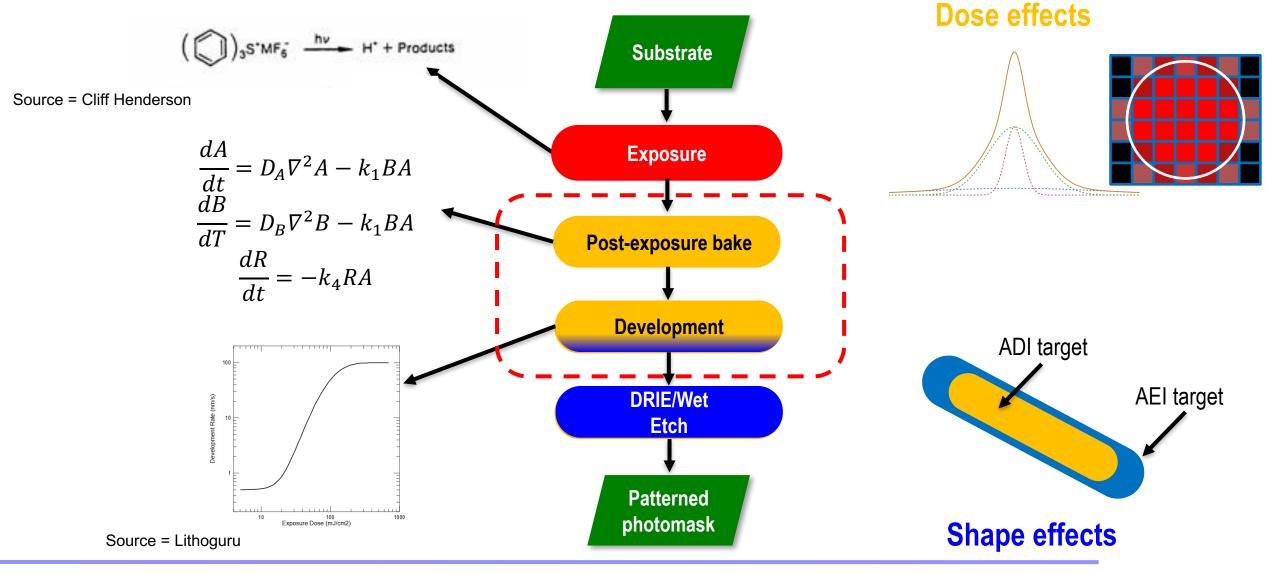


<200nm = 193i assist feature

>200nm = 193i main feature

PMJ, 2017

### **Dose/Shape Separation Requires Complete Physics**

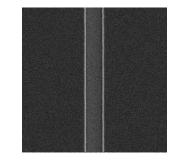


PMJ, 2017

# Must Treat Shape and Dose Effects Correctly for 193i $D_2S$

Non-zero y-axis values mean: mask print errors from model

10 10 Simulated -Measured) 8 8 6 6 Etch Fit error 4 2 0 -2 -2 -4 -6 -6 -8 -8 -10 -10 0 500 600 700 800 100 200 300 400 900 500 600 700 0 100 200 300 400 800 90 Feature width Feature width Non-separable "standard" models Separable dose and Do not meet specification shape mask models **Meet specification!** 

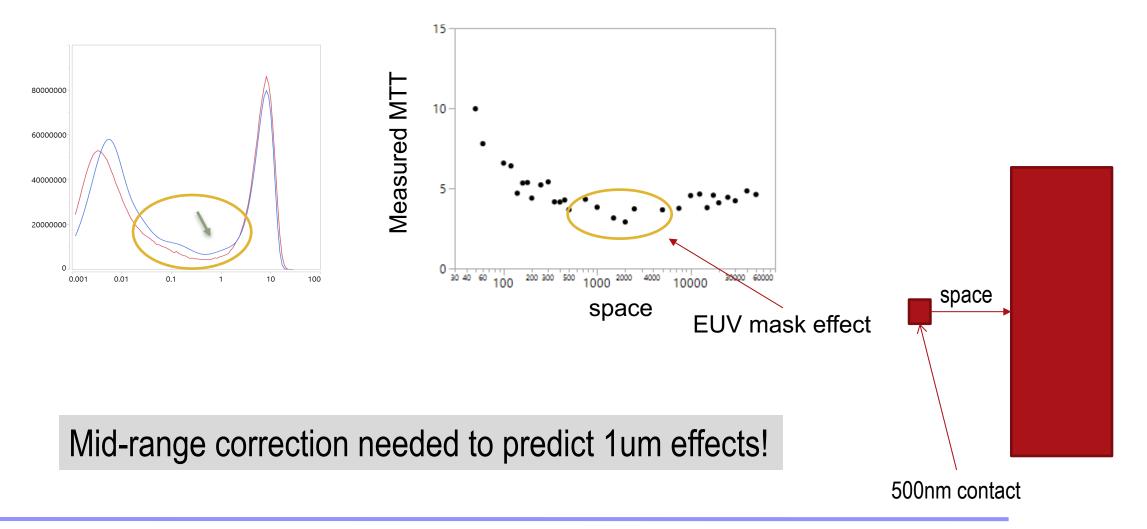


Iso Lines

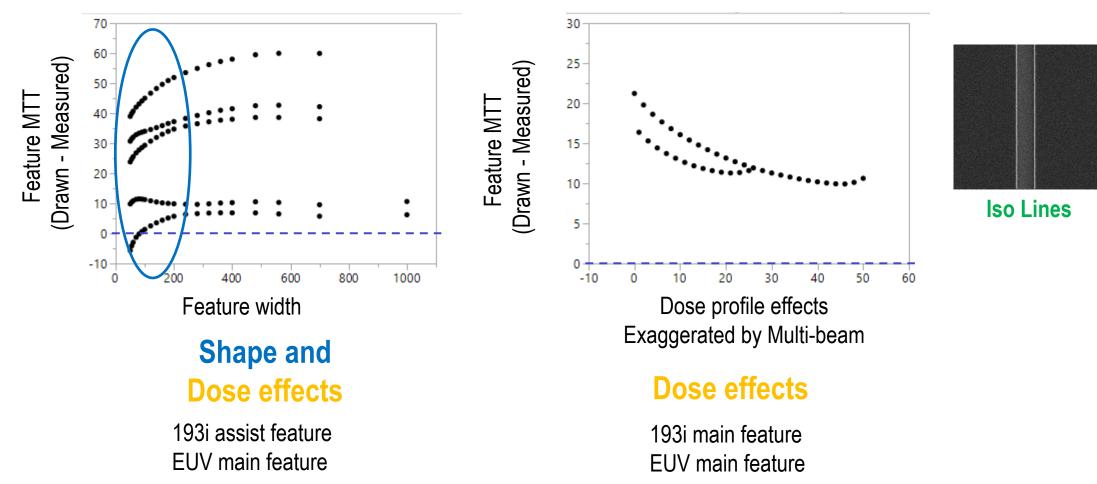
## D<sub>2</sub>S

### **EUV Mask Data Adds Mid-Range Effects**

Non-zero y-axis values mean: mask print errors if uncorrected

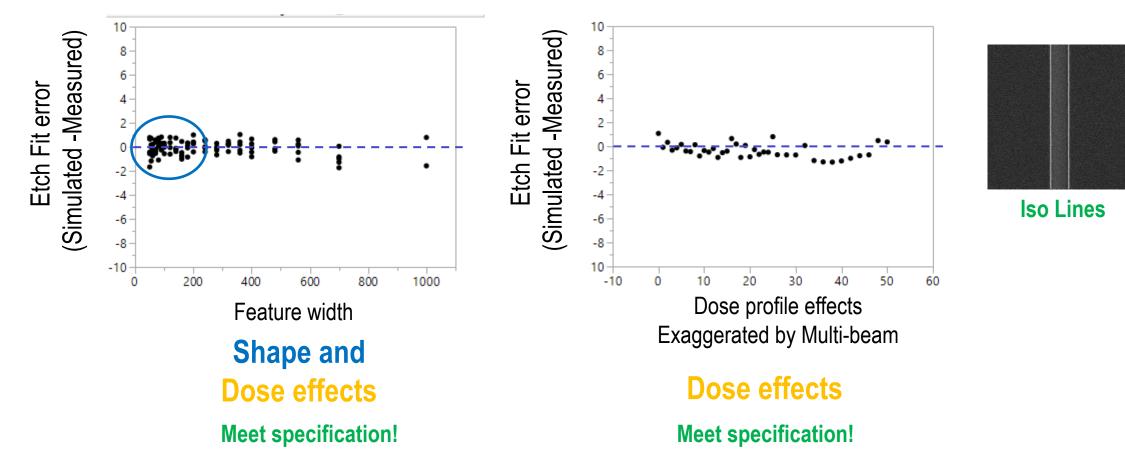


### **Must Treat Shape and EUV Dose Effects Correctly**



Non-zero y-axis values mean: mask print errors if uncorrected

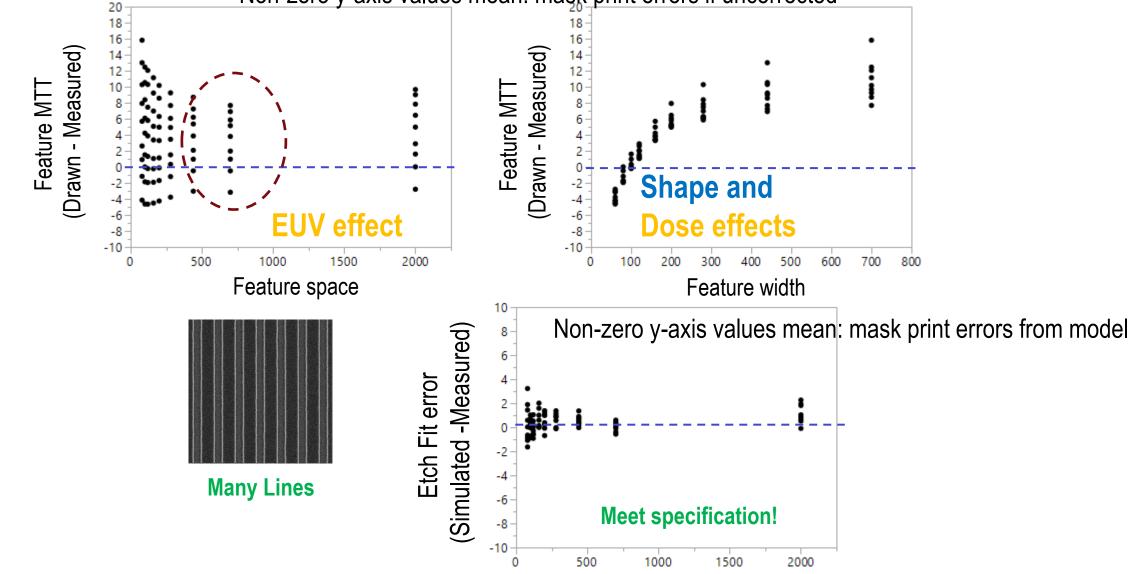
### **Must Treat Shape and EUV Dose Effects Correctly**



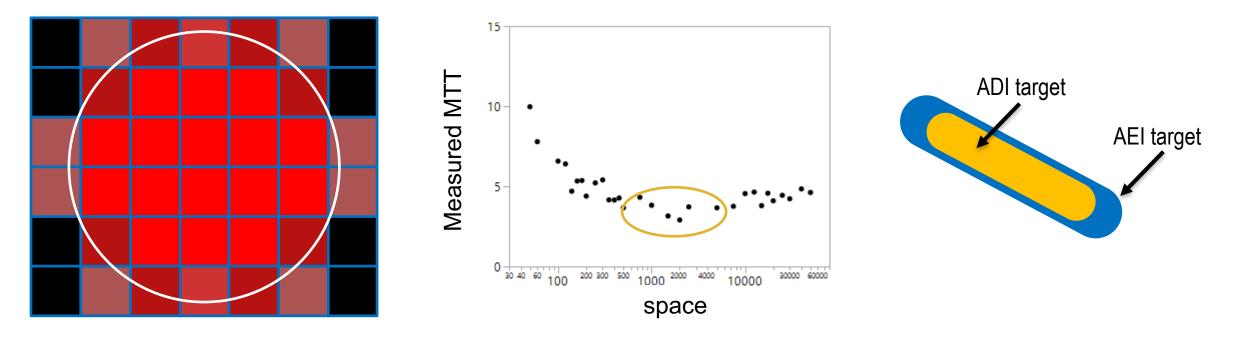
Non-zero y-axis values mean: mask print errors from model

### Must Treat Shape and EUV Dose Effects Correctly

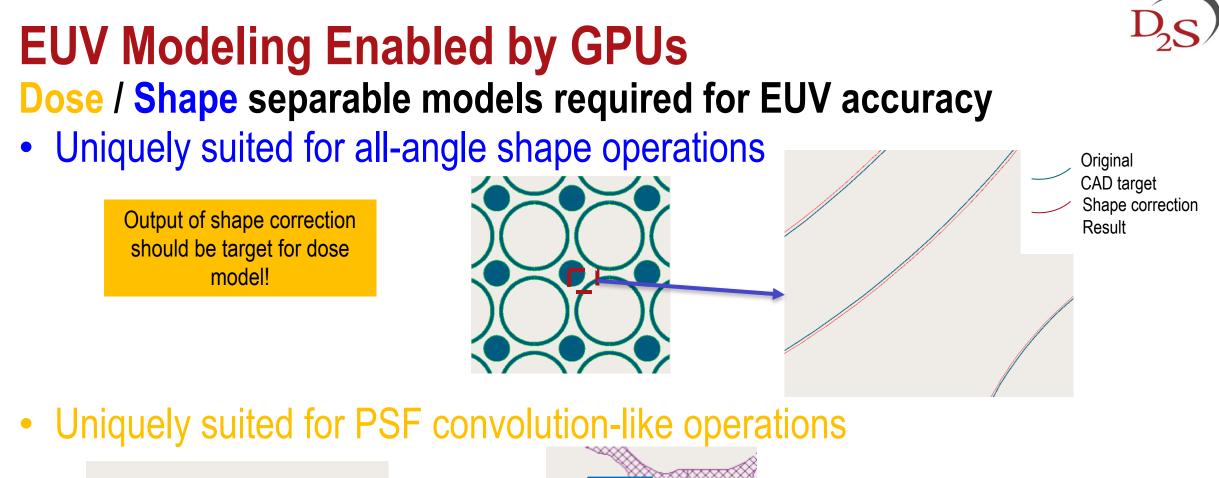
Non-zero y-axis values mean: mask print errors if uncorrected

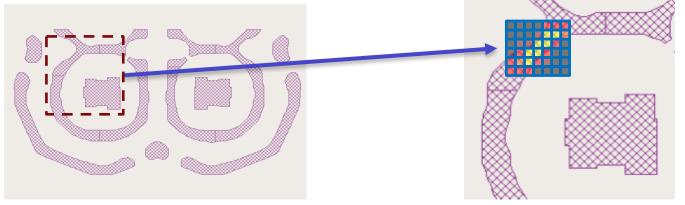


# The EUV Multi-beam Era Requires Advanced Modeling $P_2S$



#### Complex Dose effects combined with Curvilinear Shape effects mean Dose / Shape separable models required for EUV accuracy specifications





Complex dose profiles can be computed in real-time!

